



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-363 Plastic-Encapsulate DIODE

BAV99DW

SWITCHING DIODE

SOT-363



FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^{\circ}C$)

Collector current

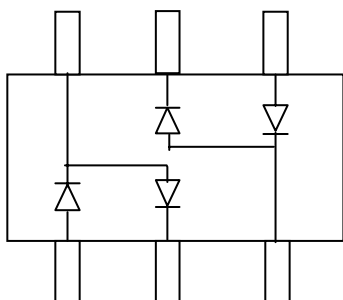
I_F : 150 mA

Collector-base voltage

V_R : 75 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



MAKING: KJG

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$	75		V
Reverse voltage leakage current	I_R	$V_R=75V$ $V_R=20V$		2.5 0.025	μA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		715 855 1000 1250	mV
Junction capacitance	C_j	$V_R=0V, f=1MHz$		2	pF
Reveres recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{rr}=0.1\times I_R$ $R_C=100\Omega$		4	nS

Typical Characteristics

BAV99DW

